

SPECIFICATION OF LED CHIP CN850-802 [INFRARED]

1) Commodity Type and Physical Characteristics.

1. Material	GaAlAs/GaAlAs (DDH)	
2. Electrode	Top Side	P (anode) side : Au Alloy
	Bottom Side	N (cathode) side : Au Alloy
3. Electrode Pattern	120um dia.	
4. Chip Size	800um*800um	
5. Chip Thickness	150um±30um	

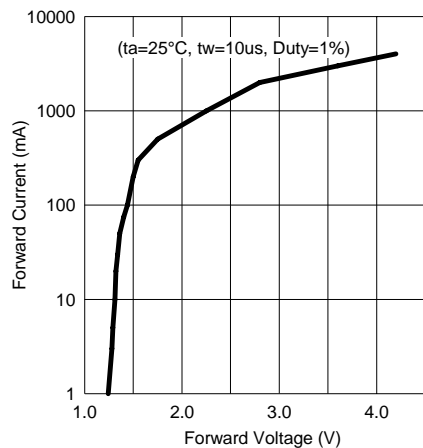
2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=50mA		1.40	1.45	V
		If=100mA		1.48	1.50	
		If=1A*		2.2	2.8	
		If=2A*		3.6	4.2	
		If=4A*		4.2	4.8	
Reverse Current	Ir	Vr=5V			10	uA
Total Radiated Power	Po	If=50mA		8.5		mW
		If=100mA		17		
		If=1A*		170		
		If=2A*		340		
		If=4A*		680		
Peak Wavelength	λ_P	If=50mA	840	850	860	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=50mA		40		nm
RiseTime	tr	If=50mA		15		ns
FallTime	tf	If=50mA		10		ns

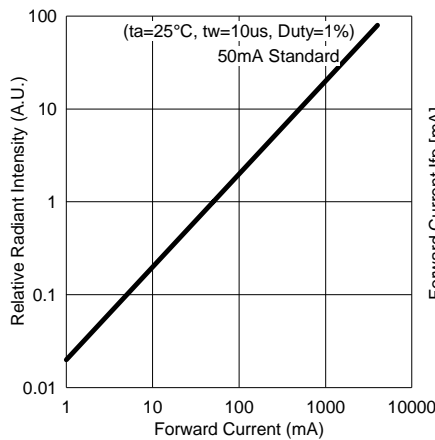
‡*Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡ Die shall be mounted on TO-18 gold header without resin coated. (Ta=25°C)

Forward Current - Forward Voltage



Relative Radiant Intensity - Forward Current



Forward Current - Pulse Duration

